## **2SB0938, 2SB0938A** (2SB938, 2SB938A)

## Silicon PNP epitaxial planar type Darlington

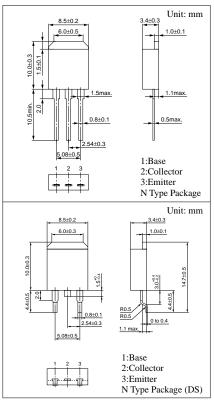
For power amplification and switching Complementary to 2SD1261 and 2SD1261A

#### Features

- High foward current transfer ratio h<sub>FE</sub>
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

### Absolute Maximum Ratings (T<sub>C</sub>=25°C)

Parameter		Symbol	Ratings	Unit	
Collector to	2SB0938	V	-60	V	
base voltage	2SB0938A	$V_{CBO}$	-80		
Collector to	2SB0938	37	-60	V	
emitter voltage	2SB0938A	$V_{CEO}$	-80		
Emitter to base voltage		$V_{\rm EBO}$	-5	V	
Peak collector current		$I_{CP}$	-8	A	
Collector current		$I_{C}$	-4	A	
Collector power	T <sub>C</sub> =25°C	D	40	W	
dissipation	Ta=25°C	$P_{C}$	1.3		
Junction temperature		$T_{j}$	150	°C	
Storage temperature		$T_{\rm stg}$	-55 to +150	°C	

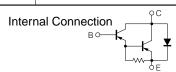


#### Electrical Characteristics (T<sub>C</sub>=25°C)

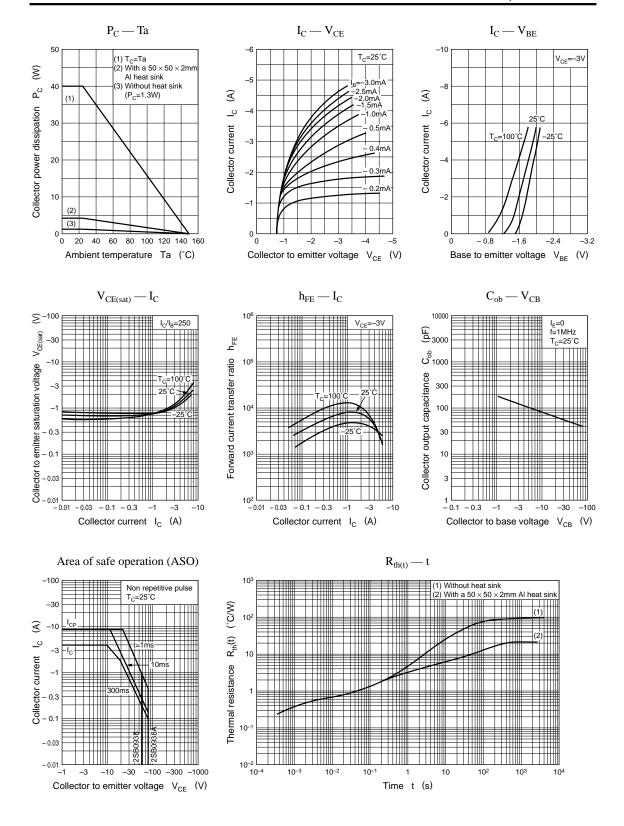
Parameter		Symbol	Conditions	min	typ	max	Unit	
Collector cutoff	2SB0938	T	$V_{CB} = -60V, I_{E} = 0$			-200		
current	2SB0938A	I <sub>CBO</sub>	$V_{CB} = -80V, I_{E} = 0$			-200	μΑ	
Collector cutoff	2SB0938	I <sub>CEO</sub>	$V_{CE} = -30V, I_{B} = 0$			-500	μА	
current	2SB0938A		$V_{CE} = -40V, I_{B} = 0$			-500		
Emitter cutoff current		I <sub>EBO</sub>	$V_{EB} = -5V, I_C = 0$			-2	mA	
Collector to emitter	2SB0938	V <sub>CEO</sub>	$I_{\rm C} = -30  {\rm mA},  I_{\rm B} = 0$	-60			V	
voltage	2SB0938A			-80				
Forward current transfer ratio		h <sub>FE1</sub>	$V_{CE} = -3V, I_{C} = -0.5A$	1000				
		h <sub>FE2</sub> *	$V_{CE} = -3V, I_{C} = -3A$	2000		10000		
Base to emitter voltage		V <sub>BE</sub>	$V_{CE} = -3V, I_{C} = -3A$			-2.5	V	
Collector to emitter saturation voltage		V <sub>CE(sat)</sub>	$I_C = -3A, I_B = -12mA$			-2	37	
			$I_{\rm C} = -5A, I_{\rm B} = -20 \text{mA}$			-4	V	
Transition frequency		$f_{\mathrm{T}}$	$V_{CE} = -10V, I_{C} = -0.5A, f = 1MHz$		15		MHz	
Turn-on time		t <sub>on</sub>			0.3		μs	
Storage time		t <sub>stg</sub>	$I_C = -3A$ , $I_{B1} = -12mA$ , $I_{B2} = 12mA$		2		μs	
Fall time		t <sub>f</sub>			0.5		μs	

## \*h<sub>FE2</sub> Rank classification

Rank	Q	P
h <sub>FE2</sub>	2000 to 5000	4000 to 10000



Note) The part numbers in the parenthesis show conventional part number.



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